

N Channel Power MOSFET with low RDS(on)

Chip Specification

General Description:

- * Advanced Process Technology
- * Dynamic dV/dt Rating
- * **150°C Operating Temperature**
- * **Fast Switching**
- * **Fully Avalanche Rated**
- * **Low RDS(on)**

Mechanical Data:

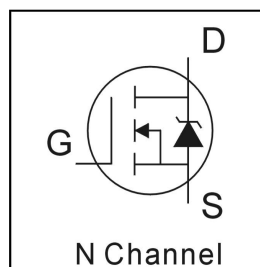
D22

Dimension **4.32mm x 5.76mm**Thickness: **400 μm**

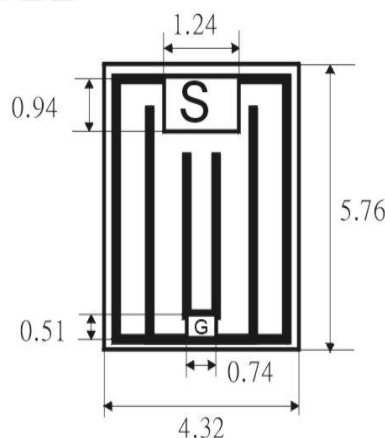
Metallization:

Top : : **Al**Backside : **CrNiAg / Au**

Suggested Bonding Conditions:

Die Mounting: **Solder Perform****95/5 PbSn or 92.5/2.5/5 PbAgIn**Source Bonding Wire: **12 mil Al**

D22



400V,500V,600V, N Channel

Absolute Maximum Rating

@Ta=25°C

Characteristics	Symbol	Limit	Unit	Test Conditions
Drain-to-Source Breakdown Voltage	V(BR)DSS	500	V	VGS=0V, ID=250μA
Static Drain-to - Source On-resistance	RDS(ON)	0.85	Ω	VGS=10V, ID=4A
Continuous Drain current (in target package)	ID@25°C	8	A	VGS=10V
Continuous Drain current (in target package)	ID@100°C	5.1	A	VGS=10V
Operation Junction	Tj	-55~150	°C	
Storage Temperature	TSTR	-55~150	°C	

Target Device: IRF840

TO-220AB

PD

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W

@Tc=25°C